

List of Publications of Prof. Stefano Ossicini

1. Band-offset driven efficiency of the doping of SiGe core-shell nanowires
M. Amato, S. Ossicini, R. Rurali
NANO LETTERS 2011 ; 11 Pages: 594 - 598
2. Self-Energy and Excitonic Effects in the Electronic and Optical Properties of TiO₂ crystalline phases
L. Chiodo, J. M. Garcia-Lastra, A. Iacomino, S. Ossicini, J. Zhao, H. Petek, A. Rubio
PHYSICAL REVIEW. B, CONDENSED MATTER AND MATERIALS PHYSICS. 2010 ; 82
Pages: 0452 - 0452
3. Segregation, quantum confinement effect and band offset for [110] SiGe NWs
M. Amato, M. Palummo, S. Ossicini
PHYSICA STATUS SOLIDI B-BASIC RESEARCH. 2010 ; 247 Pages: 2096 - 2101
4. Ab initio optoelectronic properties of SiGe nanowires: Role of many-body effects
M. Palummo, M. Amato, S. Ossicini
PHYSICAL REVIEW. B, CONDENSED MATTER AND MATERIALS PHYSICS. 2010 ; 82
Pages: 0733 – 0733
5. Many-body effects on the electronic and optical properties of Si nanowires from ab-initio approaches
M. Palummo, S. Ossicini, R. Del Sole
PHYSICA STATUS SOLIDI B-BASIC RESEARCH. 2010 ; 247 Pages: 2089 – 2095
6. Giant excitonic exchange splitting in Si nanowires: First-principle calculations
M. Palummo, F. Iori, R. Del Sole, S. Ossicini
PHYSICAL REVIEW. B, CONDENSED MATTER AND MATERIALS PHYSICS. 2010 ; 81
Pages: 1213 - 1213
7. Electronic and optical properties of Si and Ge nanocrystals: an ab-initio study
Olivia Pulci, Elena Degoli, Federico Iori, Margherita Marsili, Maurizia Palummo, Rodolfo Del Sole, Stefano Ossicini
SUPERLATTICES AND MICROSTRUCTURES. 2010 ; 47 Pages: 178 - 181
8. Local-fields and disorder effects in free-standing and embedded Si nanocrystallites
R. Guerra, E. Degoli, M. Marsili, O. Pulci, S. Ossicini
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9. Conditions for High Luminescence in Si/SiO₂ Nanocrystals
R. Guerra, S. Ossicini
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Pages: 2453 - 2453
10. Silicon and Germanium Nanostructures for Photovoltaic Applications: Ab-Initio Results
S. Ossicini, M. Amato, R. Guerra, M. Palummo, O. Pulci
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11. Engineering quantum confined silicon nanostructures: ab-initio study of the structural, electronic and optical properties

E. Degoli, S. Ossicini

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12. Ab-initio calculations of luminescence and optical gain properties in silicon nanostructures

E. DEGOLI; R. GUERRA; F. IORI; R. MAGRI; I. MARRI; O. PULCI; O. BISI; S. OSSICINI

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13. Effects of simultaneous doping with boron and phosphorous on the structural, electronic and optical properties of silicon nanostructures

F. Iori, S. Ossicini

PHYSICA E-LOW-DIMENSIONAL SYSTEMS & NANOSTRUCTURES. 2009 ; 41 Pages: 939 - 946

14. Impurity screening in silicon nanocrystals

F. Trani, D. Ninno, G. Cantele, E. Degoli, S. Ossicini

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15. Reduced quantum confinement effect and electron-hole separation in SiGe nanowires

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17. Size, oxidation, and strain in small Si/SiO₂ nanocrystals

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